

Fast Switching Speed Diodes

KMP1340-079

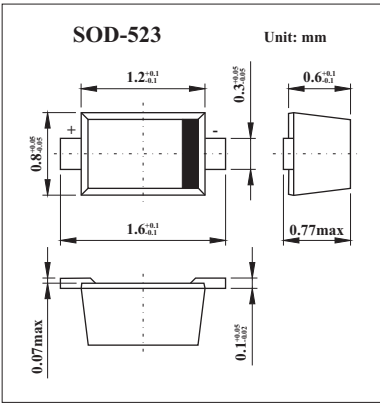
Features

Designed for Fast Speed Wireless Switch Applications

Multiple Package Configurations

Designed for High Volume Wireless Applications

Ls = 0.7 nH



Absolute Maximum Ratings Ta = 25°C

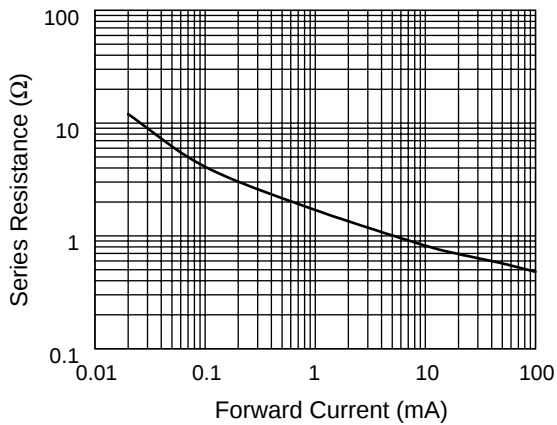
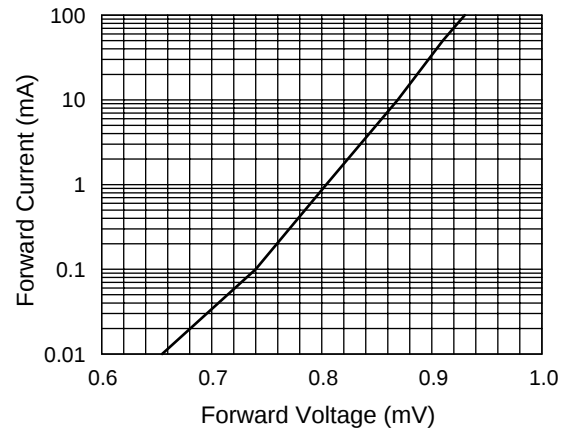
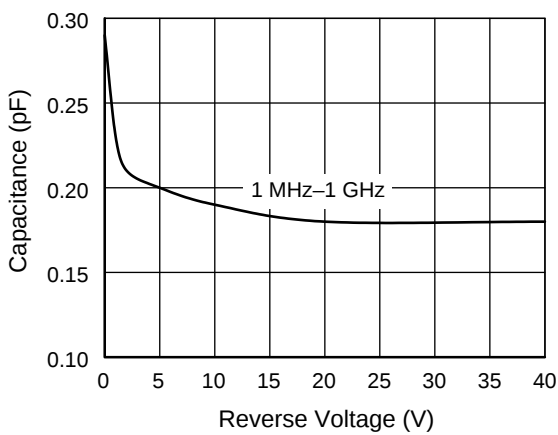
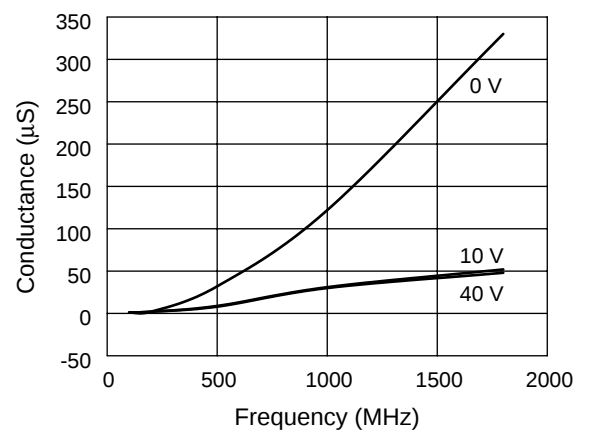
Parameter	Symbol	Ratings	Units
continuous reverse voltage	VR	50	V
total power dissipation	PD	250	mW
Junction temperature	TJ	-65 to +150	°C
Storage temperature	Tstg	-65 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF=10mA		0.85		V
Reverse current	IR	VR=50V			10	μA
Capacitance	CT	f= 1 MHz, V = 5 V		0.22	0.30	pF
Resistance	Rs	f = 100 MHz, I = 1 mA		1.8		Ω
		f = 100 MHz, I = 5 mA		1.1	2.0	Ω
		f= 100 MHz, I = 10 mA		0.9	1.2	Ω
Carrier Lifetime	TI	IF = 10 mA		100		nS
I Region Width				0.80		μm

Marking

Marking	K5
---------	----

KMP1340-079**Series Resistance vs. Current @ 100 MHz****DC Characteristic****Capacitance vs. Reverse Voltage****Conductance vs. Frequency**